UB-Suffix Series CMOS Gates

The UB Series logic gates are constructed with P and N channel enhancement mode devices in a single monolithic structure (Complementary MOS). Their primary use is where low power dissipation and/or high noise immunity is desired. The UB set of CMOS gates are inverting non–buffered functions.

Features

- Supply Voltage Range = 3.0 Vdc to 18 Vdc
- Linear and Oscillator Applications
- Capable of Driving Two Low-Power TTL Loads or One Low-Power Schottky TTL Load Over the Rated Temperature Range
- Double Diode Protection on All Inputs
- Pin–for–Pin Replacements for Corresponding CD4000 Series UB Suffix Devices
- NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable
- This Device is Pb–Free and is RoHS Compliant

MAXIMUM RATINGS (Voltages Referenced to V_{SS})

Symbol	Parameter	Value	Unit
V_{DD}	DC Supply Voltage Range	-0.5 to +18.0	V
V _{in} , V _{out}	Input or Output Voltage Range (DC or Transient)	-0.5 to V _{DD} + 0.5	V
I _{in} , I _{out}	Input or Output Current (DC or Transient) per Pin	±10	mA
P _D	Power Dissipation, per Package (Note 1)	500	mW
T _A	Ambient Temperature Range	-55 to +125	°C
T _{stg}	Storage Temperature Range	-65 to +150	°C
TL	Lead Temperature (8–Second Soldering)	260	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Temperature Derating: "D/DW" Package: -7.0 mW/°C From 65°C To 125°C

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high–impedance circuit. For proper operation, V_{in} and V_{out} should be constrained to the range $V_{SS} \leq (V_{in} \text{ or } V_{out}) \leq V_{DD}.$

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either V_{SS} or V_{DD}). Unused outputs must be left open.

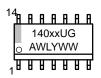


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MARKING DIAGRAM



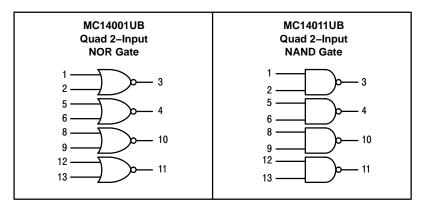
xx = Specific Device Code A = Assembly Location

WL, L = Wafer Lot YY, Y = Year WW, W = Work Week G = Pb-Free Package

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 4 of this data sheet.

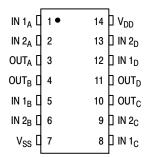
LOGIC DIAGRAMS



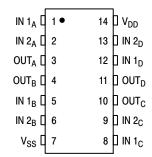
 V_{DD} = PIN 14 V_{SS} = PIN 7 FOR ALL DEVICES

PIN ASSIGNMENTS

MC14001UB Quad 2-Input NOR Gate



MC14011UB Quad 2-Input NAND Gate



ELECTRICAL CHARACTERISTICS (Voltages Referenced to V_{SS})

				- 55	5°C		25°C		125	s°C	
Characterist	tic	Symbol	V _{DD} Vdc	Min	Max	Min	Typ (Note 2)	Max	Min	Max	Unit
Output Voltage V _{in} = V _{DD} or 0	"0" Level	V _{OL}	5.0 10 15	- - -	0.05 0.05 0.05	- - -	0 0 0	0.05 0.05 0.05	- - -	0.05 0.05 0.05	Vdc
$V_{in} = 0$ or V_{DD}	"1" Level	V _{OH}	5.0 10 15	4.95 9.95 14.95	- - -	4.95 9.95 14.95	5.0 10 15	- - -	4.95 9.95 14.95	- - -	Vdc
Input Voltage $(V_O = 4.5 \text{ Vdc})$ $(V_O = 9.0 \text{ Vdc})$ $(V_O = 13.5 \text{ Vdc})$	"0" Level	V _{IL}	5.0 10 15	- - -	1.0 2.0 2.5	- - -	2.25 4.50 6.75	1.0 2.0 2.5	- - -	1.0 2.0 2.5	Vdc
$(V_O = 0.5 \text{ Vdc})$ $(V_O = 1.0 \text{ Vdc})$ $(V_O = 1.5 \text{ Vdc})$	"1" Level	V _{IH}	5.0 10 15	4.0 8.0 12.5	- - -	4.0 8.0 12.5	2.75 5.50 8.25	- - -	4.0 8.0 12.5	- - -	Vdc
Output Drive Current $(V_{OH} = 2.5 \text{ Vdc})$ $(V_{OH} = 4.6 \text{ Vdc})$ $(V_{OH} = 9.5 \text{ Vdc})$ $(V_{OH} = 13.5 \text{ Vdc})$	Source	I _{ОН}	5.0 5.0 10 15	-1.0 -0.25 -0.62 -1.8	- - -	-0.75 -0.2 -0.4 -1.5	-1.7 -0.36 -0.9 -3.5	- - -	-0.55 -0.14 -0.15 -1.0		mAdc
$(V_{OL} = 0.4 \text{ Vdc})$ $(V_{OL} = 0.5 \text{ Vdc})$ $(V_{OL} = 1.5 \text{ Vdc})$	Sink	I _{OL}	5.0 10 15	0.64 1.6 4.2	- - -	0.51 1.1 3.4	0.88 2.25 8.8	- - -	0.36 0.7 2.4	- - -	mAdc
Input Current		I _{in}	15	_	±0.1	_	±0.00001	±0.1	-	±1.0	μAdc
Input Capacitance (V _{in} = 0)		C _{in}	-	_	-	-	5.0	7.5	_	-	pF
Quiescent Current (Per Package)		I _{DD}	5.0 10 15	- - -	0.25 0.5 1.0	- - -	0.0005 0.0010 0.0015	0.25 0.5 1.0	- - -	7.5 15 30	μAdc
Total Supply Current (No (Dynamic plus Quies Per Gate C _L = 50 pf	scent,	lτ	5.0 10 15		•	$I_{T} = (0.0)$	3 μA/kHz) f + 6 μA/kHz) f + 8 μA/kHz) f +	+ I _{DD} /N	•	•	μAdc

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

- 2. Data labelled "Typ" is not to be used for design purposes but is intended as an indication of the IC's potential performance.
- 3. The formulas given are for the typical characteristics only at 25°C.
 4. To calculate total supply current at loads other than 50 pF:

$$I_T(C_L) = I_T(50 \text{ pF}) + (C_L - 50) \text{ Vfk}$$

where: I_T is in μH (per package), C_L in pF, $V = (V_{DD} - V_{SS})$ in volts, f in kHz is input frequency, and k = 0.001 x the number of exercised gates per package.

SWITCHING CHARACTERISTICS (Note 5) ($C_L = 50 \text{ pF}, T_A = 25^{\circ}\text{C}$)

Characteristic	Symbol	V _{DD} Vdc	Min	Typ (Note 6)	Max	Unit
Output Rise Time	t _{TLH}					ns
$t_{TLH} = (3.0 \text{ ns/pF}) C_L + 30 \text{ ns}$		5.0	_	180	360	
$t_{TLH} = (1.5 \text{ ns/pF}) C_L + 15 \text{ ns}$		10	_	90	180	
$t_{TLH} = (1.1 \text{ ns/pF}) C_L + 10 \text{ ns}$		15	_	65	130	
Output Fall Time	t _{THL}					ns
$t_{THL} = (1.5 \text{ ns/pF}) C_L + 25 \text{ ns}$		5.0	_	100	200	
$t_{THL} = (0.75 \text{ ns/pF}) C_L + 12.5 \text{ ns}$		10	_	50	100	
$t_{THL} = (0.55 \text{ ns/pF}) C_L + 9.5 \text{ ns}$		15	_	40	80	
Propagation Delay Time	t _{PLH} , t _{PHL}					ns
t_{PLH} , $t_{PHL} = (1.7 \text{ ns/pF}) C_L + 30 \text{ ns}$		5.0	_	90	180	
t_{PLH} , $t_{PHL} = (0.66 \text{ ns/pF}) C_L + 22 \text{ ns}$		10	_	50	100	
t_{PLH} , $t_{PHL} = (0.50 \text{ ns/pF}) C_L + 15 \text{ ns}$		15	_	40	80	

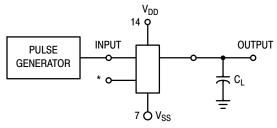
- The formulas given are for the typical characteristics only at 25°C.
- 6. Data labelled "Typ" is not to be used for design purposes but is intended as an indication of the IC's potential performance.

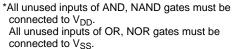
ORDERING INFORMATION

Device	Package	Shipping [†]
MC14001UBDG	SOIC-14 (Pb-Free)	55 Units / Rail
NLV14001UBDG*	SOIC-14 (Pb-Free)	55 Units / Rail
MC14001UBDR2G	SOIC-14 (Pb-Free)	2500 / Tape & Reel
NLV14001UBDR2G*	SOIC-14 (Pb-Free)	2500 / Tape & Reel
MC14011UBDG	SOIC-14 (Pb-Free)	55 Units / Rail
NI V14011LIBDG*	SOIC-14	55 Units / Rail

MC14011UBDG	SOIC-14 (Pb-Free)	55 Units / Rail
NLV14011UBDG*	SOIC-14 (Pb-Free)	55 Units / Rail
MC14011UBDR2G	SOIC-14 (Pb-Free)	2500 / Tape & Reel
NLV14011UBDR2G*	SOIC-14 (Pb-Free)	2500 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.





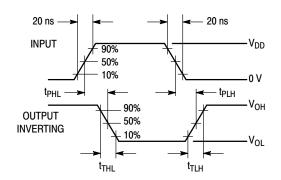
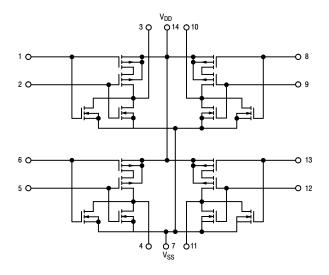


Figure 1. Switching Time Test Circuit and Waveforms

^{*}NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable.

MC14001UB CIRCUIT SCHEMATIC



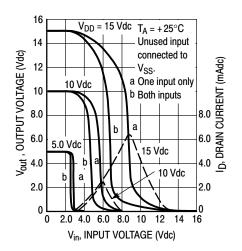


Figure 2. Typical Voltage and Current Transfer Characteristics

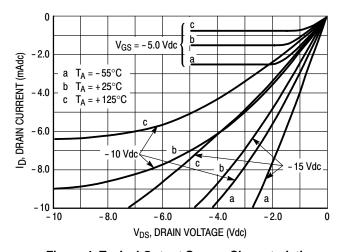
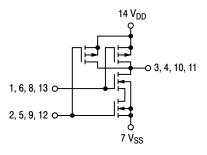


Figure 4. Typical Output Source Characteristics

MC14011UB CIRCUIT SCHEMATIC (1/4 of Device Shown)



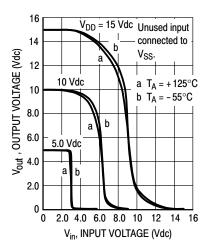


Figure 3. Typical Voltage Transfer Characteristics versus Temperature

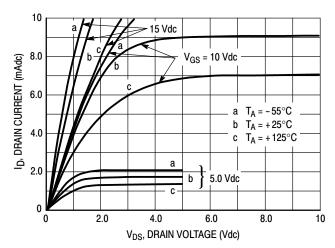


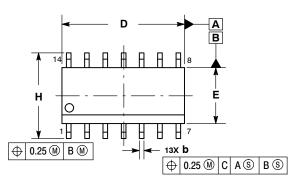
Figure 5. Typical Output Sink Characteristics



△ 0.10

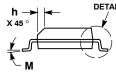
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DATE 03 FEB 2016





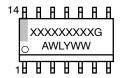




- NOTES:
 1. DIMENSIONING AND TOLERANCING PER
 - ASME Y14.5M, 1994.
 CONTROLLING DIMENSION: MILLIMETERS.
 - DIMENSION b DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE PROTRUSION SHALL BE 0.13 TOTAL IN EXCESS OF AT
- MAXIMUM MATERIAL CONDITION.
 DIMENSIONS D AND E DO NOT INCLUDE MOLD PROTRUSIONS.
- 5. MAXIMUM MOLD PROTRUSION 0.15 PER SIDE

	MILLIN	IETERS	INC	HES
DIM	MIN	MAX	MIN	MAX
Α	1.35	1.75	0.054	0.068
A1	0.10	0.25	0.004	0.010
АЗ	0.19	0.25	0.008	0.010
b	0.35	0.49	0.014	0.019
D	8.55	8.75	0.337	0.344
Е	3.80	4.00	0.150	0.157
е	1.27	BSC	0.050	BSC
Н	5.80	6.20	0.228	0.244
h	0.25	0.50	0.010	0.019
Ĺ	0.40	1.25	0.016	0.049
М	0 °	7°	0 °	7°

GENERIC MARKING DIAGRAM*



XXXXX = Specific Device Code Α = Assembly Location

WL = Wafer Lot Υ = Year WW = Work Week G = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator. "G" or microdot " ■". may or may not be present.

SOLDERING FOOTPRINT*



DIMENSIONS: MILLIMETERS

C SEATING PLANE

STYLES ON PAGE 2

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^{*}For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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DATE 03 FEB 2016

STYLE 1: PIN 1. COMMON CATHODE 2. ANODE/CATHODE 3. ANODE/CATHODE 4. NO CONNECTION 5. ANODE/CATHODE 6. NO CONNECTION 7. ANODE/CATHODE 8. ANODE/CATHODE 9. ANODE/CATHODE 10. NO CONNECTION 11. ANODE/CATHODE 12. ANODE/CATHODE 13. NO CONNECTION 14. COMMON ANODE	STYLE 2: CANCELLED	STYLE 3: PIN 1. NO CONNECTION 2. ANODE 3. ANODE 4. NO CONNECTION 5. ANODE 6. NO CONNECTION 7. ANODE 8. ANODE 9. ANODE 10. NO CONNECTION 11. ANODE 12. ANODE 13. NO CONNECTION 14. COMMON CATHODE	STYLE 4: PIN 1. NO CONNECTION 2. CATHODE 3. CATHODE 4. NO CONNECTION 5. CATHODE 6. NO CONNECTION 7. CATHODE 8. CATHODE 9. CATHODE 10. NO CONNECTION 11. CATHODE 12. CATHODE 13. NO CONNECTION 14. COMMON ANODE
STYLE 5: PIN 1. COMMON CATHODE 2. ANODE/CATHODE 3. ANODE/CATHODE 4. ANODE/CATHODE 5. ANODE/CATHODE 6. NO CONNECTION 7. COMMON ANODE 8. COMMON CATHODE 9. ANODE/CATHODE 10. ANODE/CATHODE 11. ANODE/CATHODE 12. ANODE/CATHODE 13. NO CONNECTION 14. COMMON ANODE	STYLE 6: PIN 1. CATHODE 2. CATHODE 3. CATHODE 4. CATHODE 5. CATHODE 6. CATHODE 7. CATHODE 8. ANODE 9. ANODE 10. ANODE 11. ANODE 12. ANODE 13. ANODE 14. ANODE	STYLE 7: PIN 1. ANODE/CATHODE 2. COMMON ANODE 3. COMMON CATHODE 4. ANODE/CATHODE 5. ANODE/CATHODE 6. ANODE/CATHODE 7. ANODE/CATHODE 8. ANODE/CATHODE 9. ANODE/CATHODE 10. ANODE/CATHODE 11. COMMON CATHODE 12. COMMON ANODE 13. ANODE/CATHODE 14. ANODE/CATHODE	STYLE 8: PIN 1. COMMON CATHODE 2. ANODE/CATHODE 3. ANODE/CATHODE 4. NO CONNECTION 5. ANODE/CATHODE 6. ANODE/CATHODE 7. COMMON ANODE 8. COMMON ANODE 9. ANODE/CATHODE 10. ANODE/CATHODE 11. NO CONNECTION 12. ANODE/CATHODE 13. ANODE/CATHODE 14. COMMON CATHODE

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